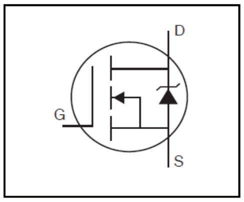
AUTOMOTIVE GRADE

AUIRF3808S

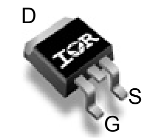
HEXFET® Power MOSFET

Features

- Advanced Planar Technology
- Low On-Resistance
- Dynamic dV/dT Rating
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified *



V_{DSS}		**75V**
$R_{DS(on)}$	typ.	**5.9mΩ**
	max.	**7.0mΩ**
I_D		**106A**



D²Pak
AUIRF3808S

G	D	S
Gate	Drain	Source

Description

Specifically designed for Automotive applications, this Stripe Planar design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRF3808S	D²-Pak	Tube	50	AUIRF3808S
		Tape and Reel Left	800	AUIRF3808STRL

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (TA) is 25°C, unless otherwise specified.

Symbol	Parameter	Max.	Units
I_D @ T_C = 25°C	Continuous Drain Current, V_{GS} @ 10V	106	A
I_D @ T_C = 100°C	Continuous Drain Current, V_{GS} @ 10V	75	
I_{DM}	Pulsed Drain Current ①	550	
P_D @T_C = 25°C	Maximum Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	430	mJ
I_{AR}	Avalanche Current ①	82	A
E_{AR}	Repetitive Avalanche Energy ⑤	See Fig. 12a, 12b, 15, 16	mJ
dv/dt	Peak Diode Recovery ③	5.5	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds (1.6mm from case)	300	

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case⑧	——	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, steady state) ⑦		40	

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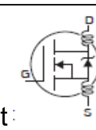
*Qualification standards can be found at www.infineon.com

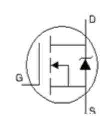
Static @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	75	–––	–––	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	–––	0.086	–––	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	–––	5.9	7.0	mΩ	V_{GS} = 10V, I_D = 82A ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	–––	4.0	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	100	–––	–––	S	V_{DS} = 25V, I_D = 82A
I_{DSS}	Drain-to-Source Leakage Current	–––	–––	25	µA	V_{DS} = 75V, V_{GS} = 0V
		–––	–––	250		V_{DS} = 60V,V_{GS} = 0V,T_J =150°C
I_{GSS}	Gate-to-Source Forward Leakage	–––	–––	200	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	–––	–––	-200		V_{GS} = -20V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge	–––	150	220	nC	I_D = 82A
Q_{gs}	Gate-to-Source Charge	–––	31	47		V_{DS} = 60V
Q_{gd}	Gate-to-Drain Charge	–––	50	76		V_{GS} = 10V④
$t_{d(on)}$	Turn-On Delay Time	–––	16	–––	ns	V_{DD} = 38V
t_r	Rise Time	–––	140	–––		I_D = 82A
$t_{d(off)}$	Turn-Off Delay Time	–––	68	–––		R_G= 2.5Ω,
t_f	Fall Time	–––	120	–––		V_{GS} = 10V④
L_D	Internal Drain Inductance	–––	4.5	–––	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
L_S	Internal Source Inductance	–––	7.5	–––		
C_{iss}	Input Capacitance	–––	5310	–––	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	–––	890	–––		V_{DS} = 25V
C_{rss}	Reverse Transfer Capacitance	–––	130	–––		f = 1.0MHz, See Fig.5
C_{oss}	Output Capacitance	–––	6010	–––		V_{GS} = 0V,V_{DS} = 1.0V, f = 1.0MHz
C_{oss}	Output Capacitance	–––	570	–––		V_{GS} = 0V,V_{DS} = 60V, f = 1.0MHz
$C_{oss\ eff.}$	Effective Output Capacitance (Time Related)	–––	1140	–––		V_{GS} = 0V,V_{DS} = 0V to 60V

Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	–––	–––	106	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	–––	–––	550		
V_{SD}	Diode Forward Voltage	–––	–––	1.3	V	T_J = 25°C,I_S = 82A,V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	–––	93	140	ns	T_J = 25°C ,I_F = 82A
Q_{rr}	Reverse Recovery Charge	–––	340	510	nC	di/dt = 100A/µs ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig.11)
② Starting T_J = 25°C, L = 0.130mH, R_G = 25Ω, I_{AS} = 82A. (See fig.12)
③ $I_{SD} \leq$ 82A, di/dt $\leq$ 310A/µs, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq$ 175°C.
④ Pulse width $\leq$ 400µs; duty cycle $\leq$ 2%.
⑤ $C_{oss\ eff.}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .
⑥ Limited by T_{Jmax} , see Fig.12a, 12b, 15, 16 for typical repetitive avalanche performance.
⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994
⑧ R_θ is measured at T_J of approximately 90°C

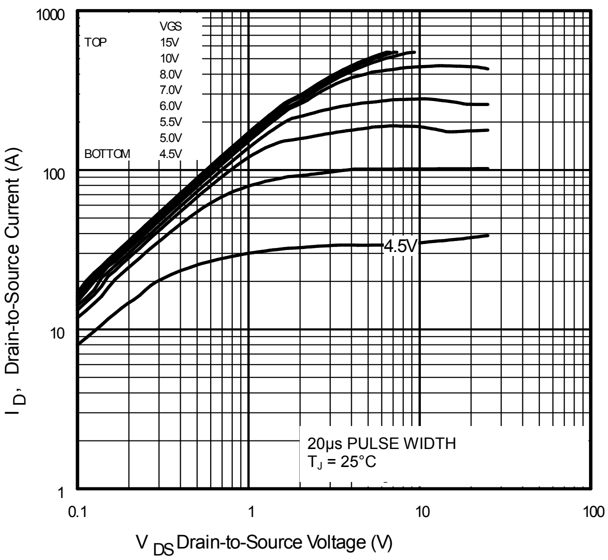


Fig. 1 Typical Output Characteristics

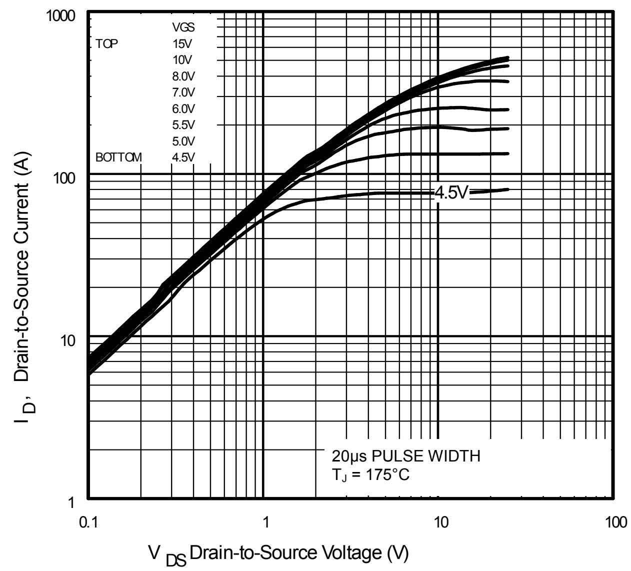


Fig. 2 Typical Output Characteristics

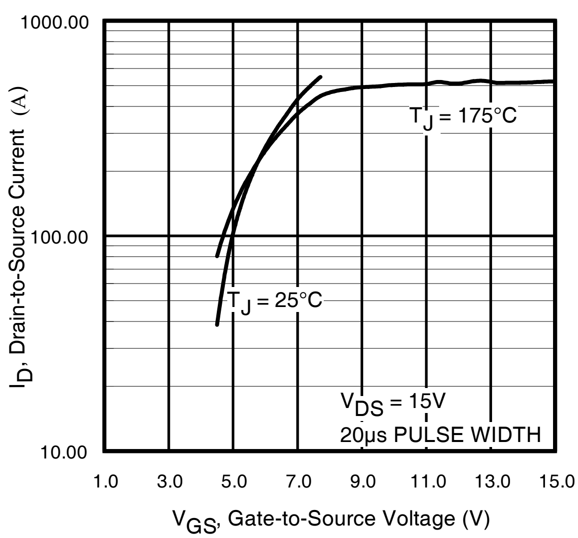


Fig. 3 Typical Transfer Characteristics

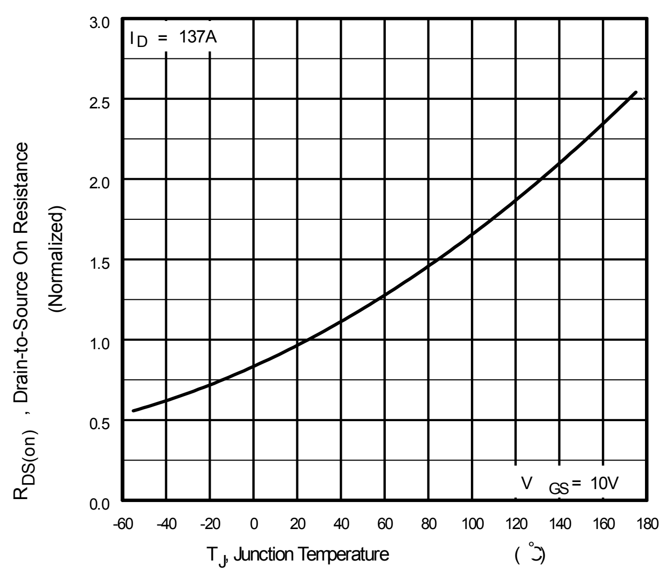


Fig. 4 Normalized On-Resistance vs. Temperature

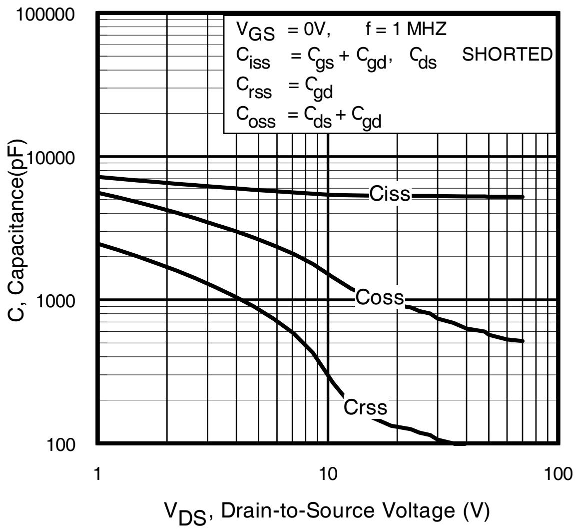


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage

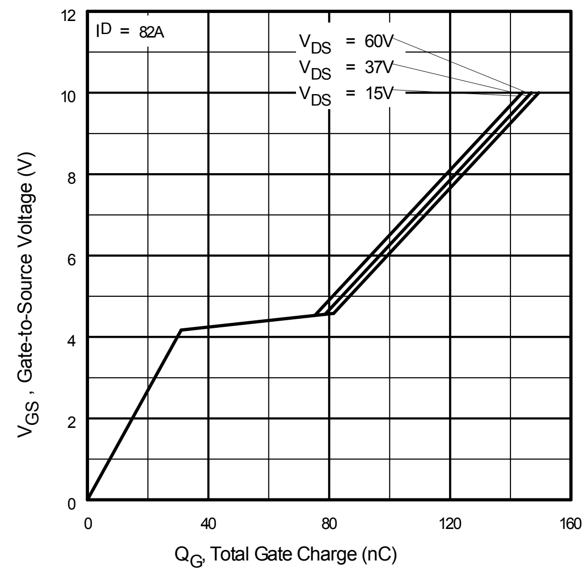


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

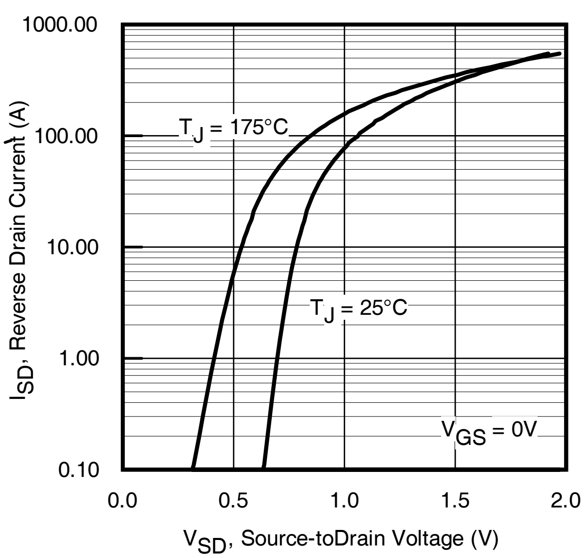


Fig. 7 Typical Source-to-Drain Diode Forward Voltage

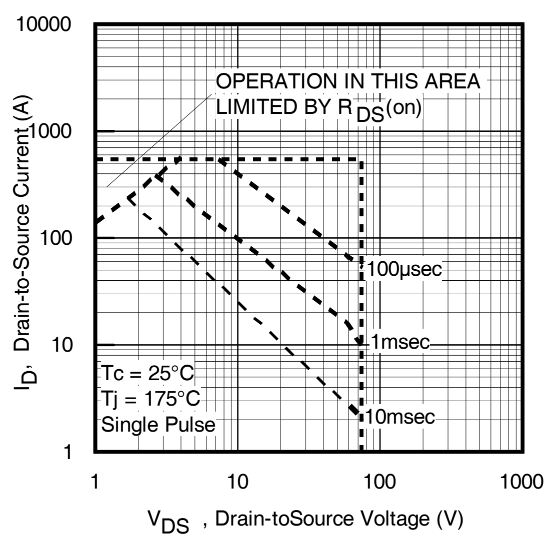


Fig 8. Maximum Safe Operating Area

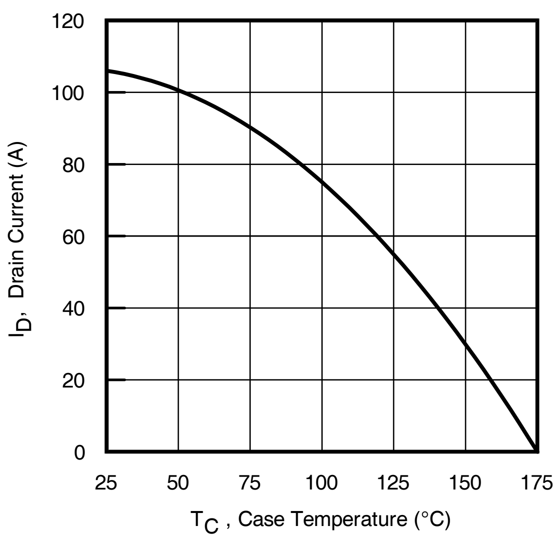


Fig 9. Maximum Drain Current vs. Case Temperature

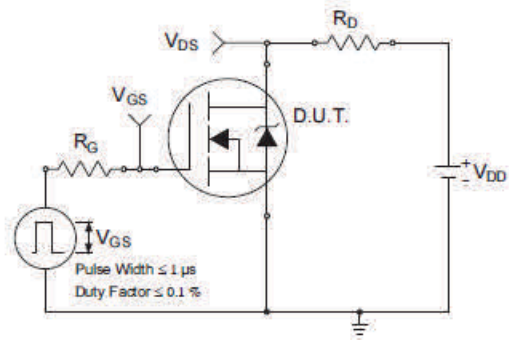


Fig 10a. Switching Time Test Circuit

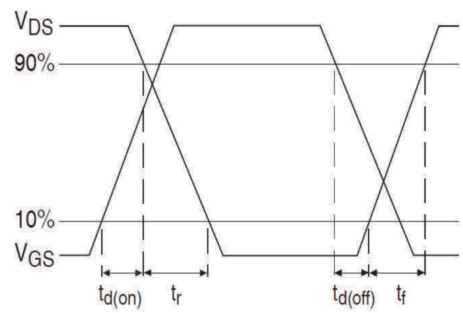


Fig 10b. Switching Time Waveforms

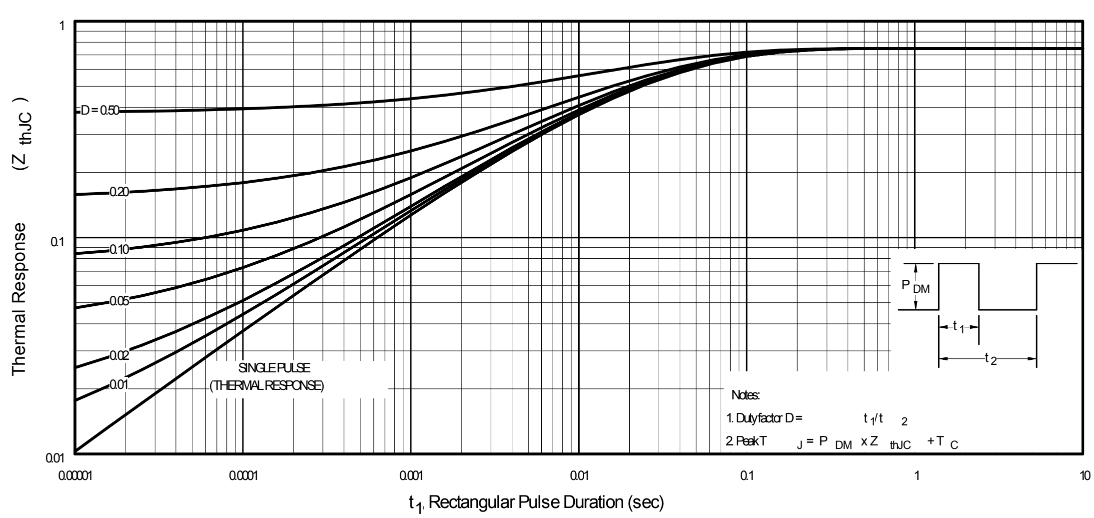


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

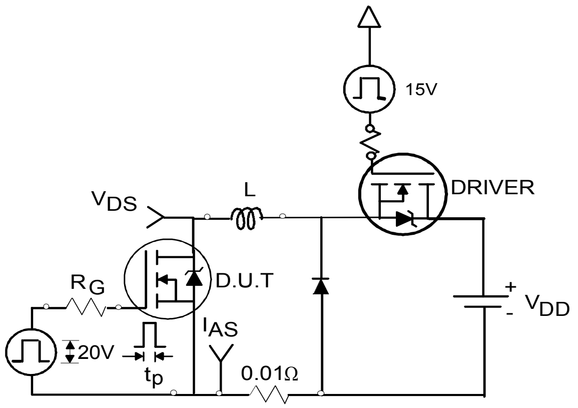


Fig 12a. Unclamped Inductive Test Circuit

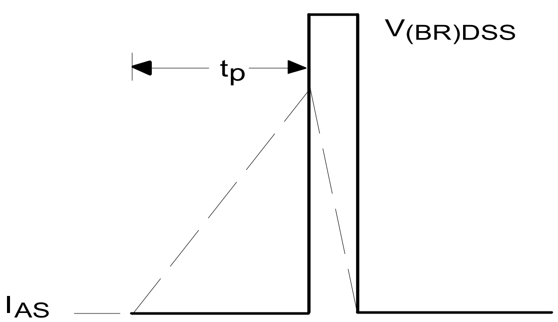


Fig 12b. Unclamped Inductive Waveforms

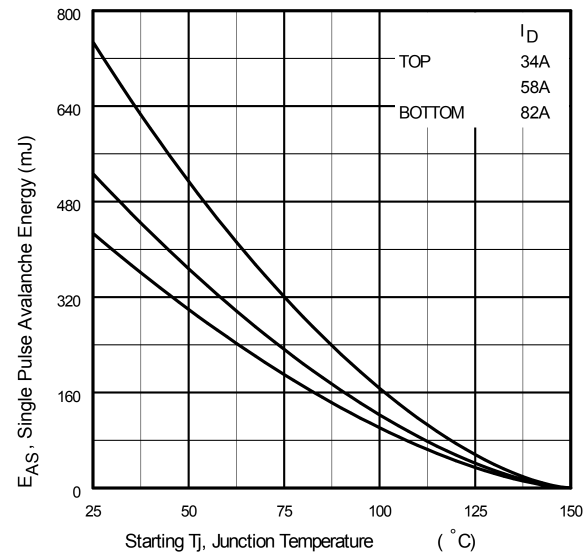


Fig 12c. Maximum Avalanche Energy vs. Drain Current

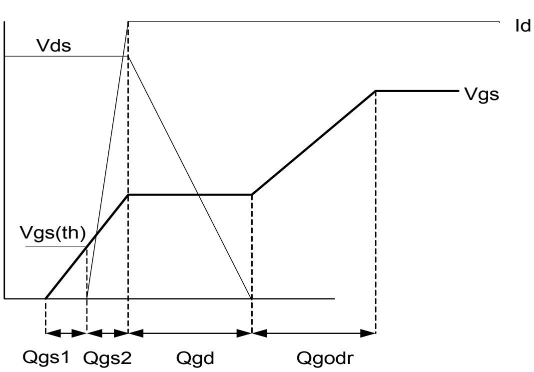


Fig 13a. Gate Charge Waveform

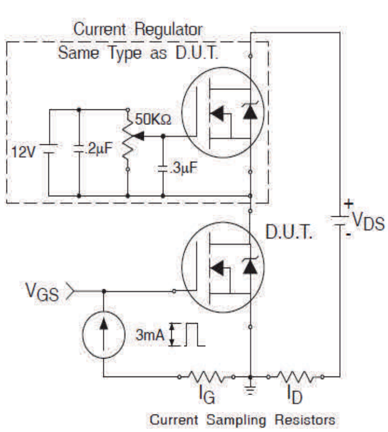


Fig 13b. Gate Charge Test Circuit

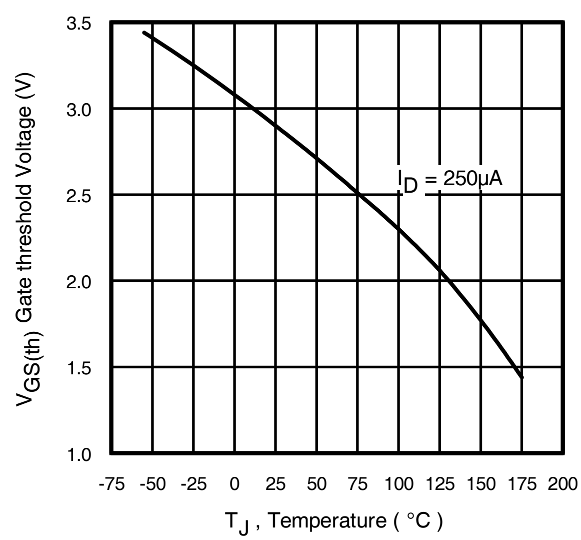


Fig 14. Threshold Voltage vs. Temperature

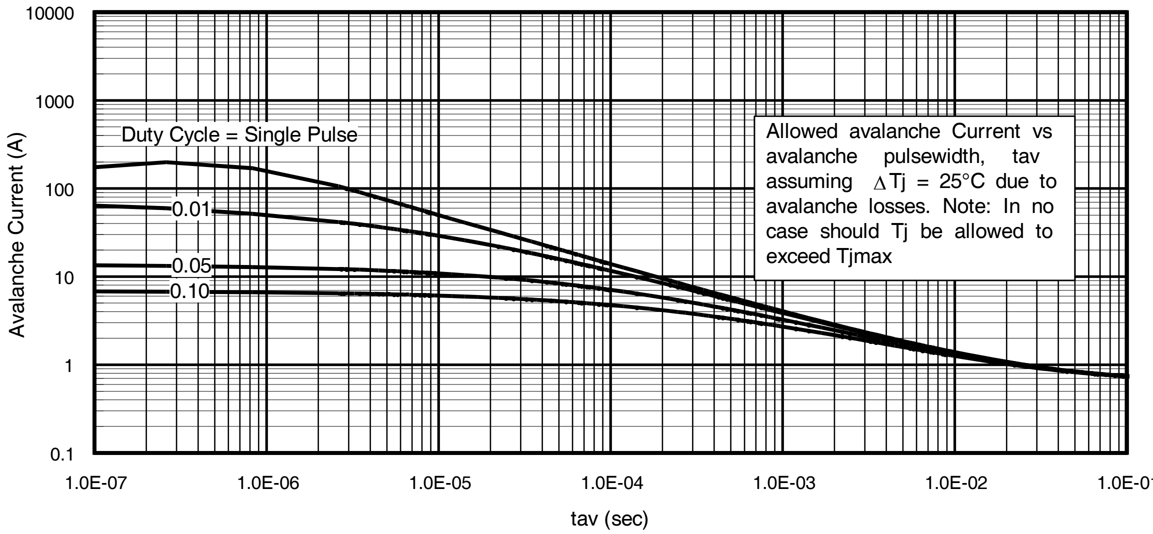


Fig 15. Typical Avalanche Current vs. Pulse width

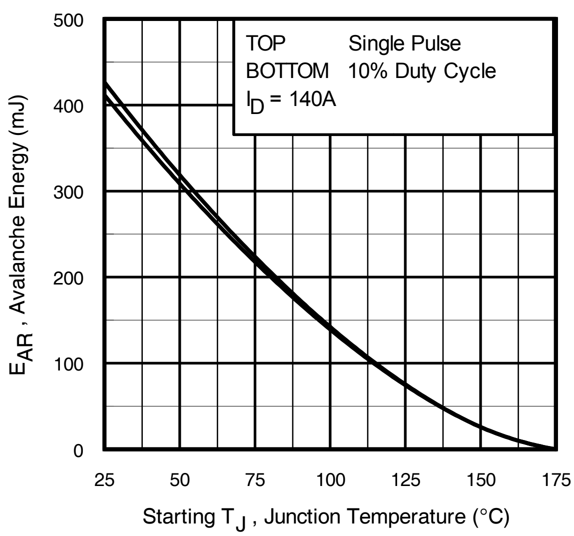


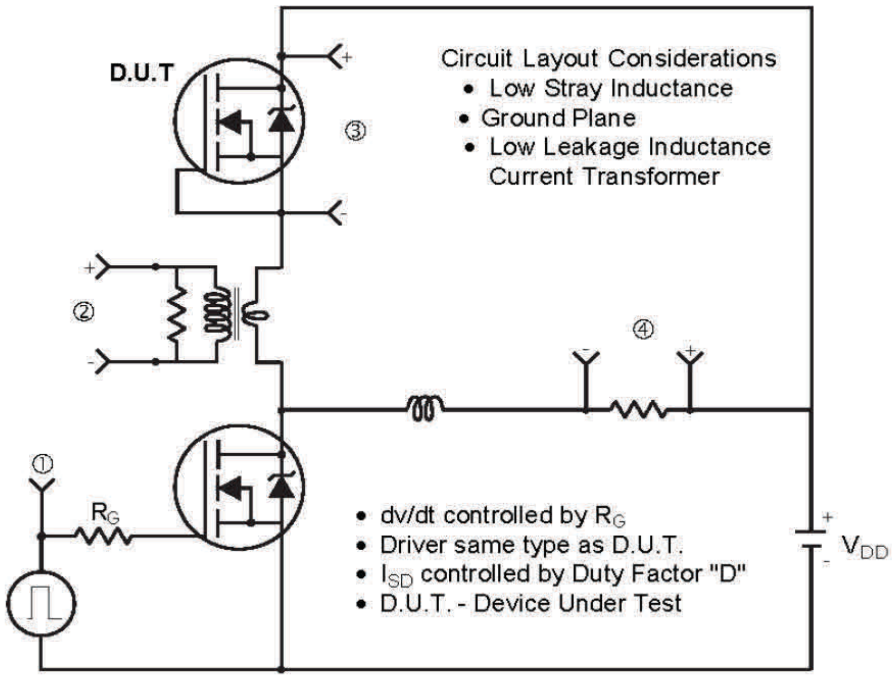
Fig 16. Maximum Avalanche Energy vs. Temperature

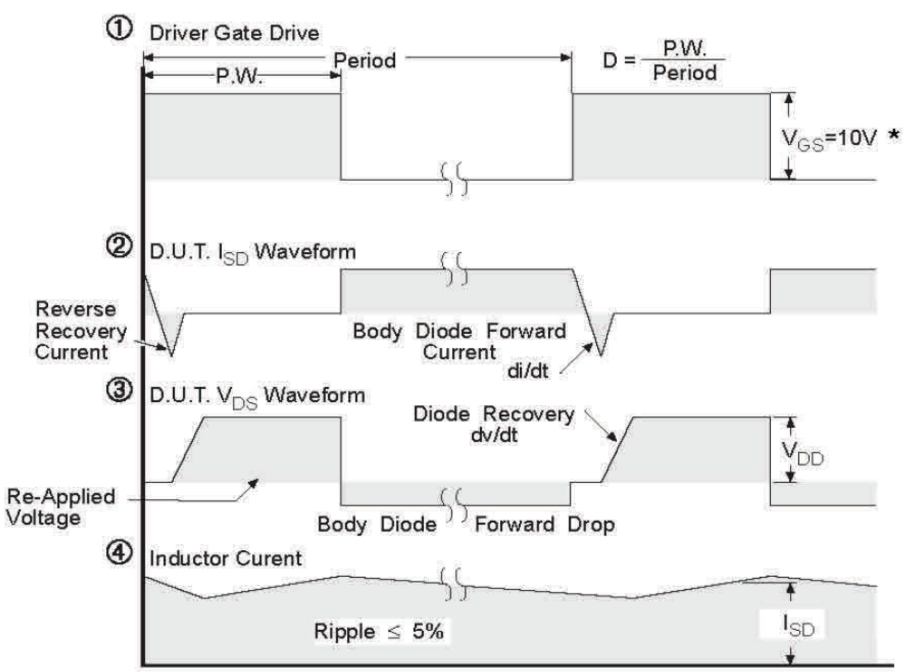
Notes on Repetitive Avalanche Curves , Figures 15, 16:
(For further info, see AN-1005 at www.infineon.com)

1. Avalanche failures assumption:
   Purely a thermal phenomenon and failure occurs at a temperature far in excess of T_{jmax}. This is validated for every part type.
2. Safe operation in Avalanche is allowed as long as T_{jmax} is not exceeded.
3. Equation below based on circuit and waveforms shown in Figures 12a, 12b.
4. $P_{D\ (ave)}$ = Average power dissipation per single avalanche pulse.
5. BV = Rated breakdown voltage (1.3 factor accounts for voltage increase during avalanche).
6. I_{av} = Allowable avalanche current.
7. ΔT = Allowable rise in junction temperature, not to exceed T_{jmax} (assumed as 25°C in Figure 15, 16).
   t_{av} = Average time in avalanche.
   D = Duty cycle in avalanche = $t_{av} \cdot f$
   $Z_{thJC}(D, t_{av})$ = Transient thermal resistance, see Figures 13)

$$P_{D\ (ave)} = 1/2\ (1.3 \cdot BV \cdot I_{av}) = \Delta T / Z_{thJC}$$
$$I_{av} = 2\Delta T / [1.3 \cdot BV \cdot Z_{th}]$$
$$E_{AS\ (AR)} = P_{D\ (ave)} \cdot t_{av}$$

Peak Diode Recovery dv/dt Test Circuit

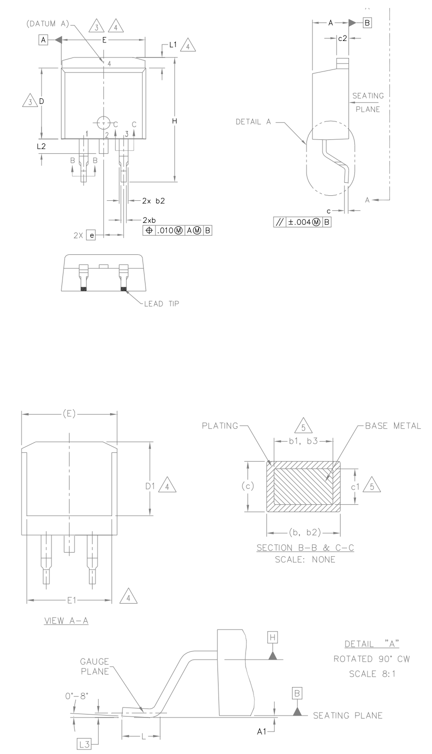




* V_{GS} = 5V for Logic Level Devices

Fig 17. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

D²Pak (TO-263AB) Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. (△) DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY AT DATUM H.
4. (△) THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSION E, L1, D1 & E1.
5. (△) DIMENSION b1, b3 AND c1 APPLY TO BASE METAL ONLY.
6. DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
7. CONTROLLING DIMENSION: INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-263AB.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	0.00	0.254	.000	.010	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.38	0.74	.015	.029	
c1	0.38	0.58	.015	.023	5
c2	1.14	1.65	.045	.065	
D	8.38	9.65	.330	.380	3
D1	6.86	–	.270	–	4
E	9.65	10.67	.380	.420	3,4
E1	6.22	–	.245	–	4
e	2.54 BSC		.100 BSC		
H	14.61	15.88	.575	.625	
L	1.78	2.79	.070	.110	
L1	–	1.68	–	.066	4
L2	–	1.78	–	.070	
L3	0.25 BSC		.010 BSC		

LEAD ASSIGNMENTS

DIODES

1.– ANODE (TWO DIE) / OPEN (ONE DIE)
2, 4.– CATHODE
3.– ANODE

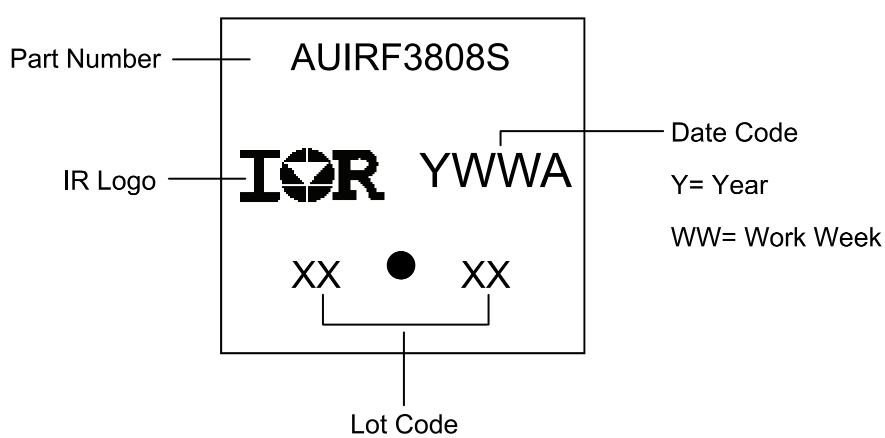
HEXFET

1.– GATE
2, 4.– DRAIN
3.– SOURCE

IGBTs, CoPACK

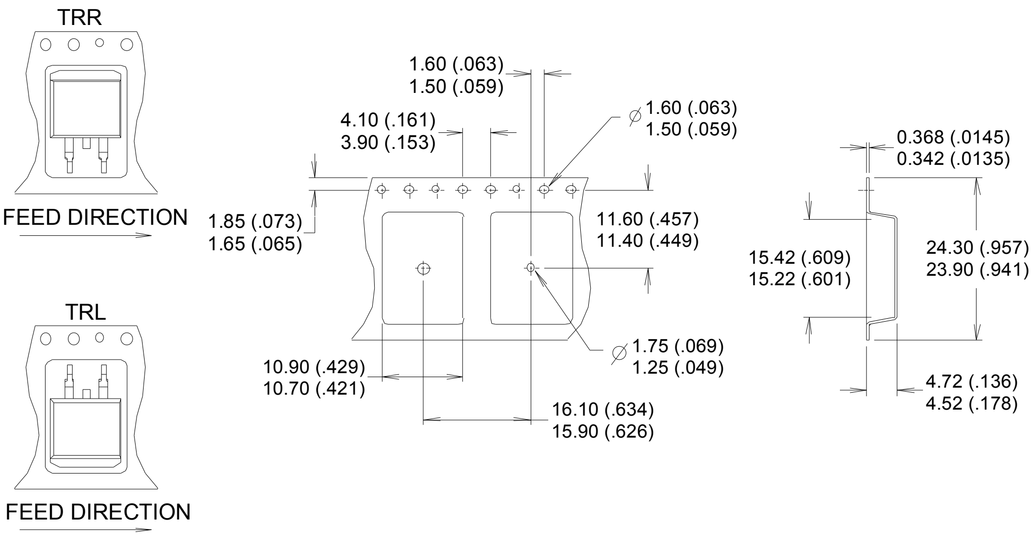
1.– GATE
2, 4.– COLLECTOR
3.– EMITTER

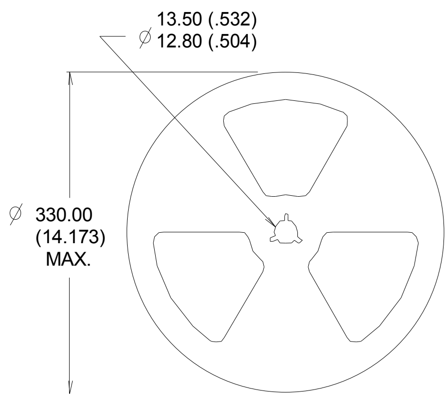
D²Pak (TO-263AB) Part Marking Information

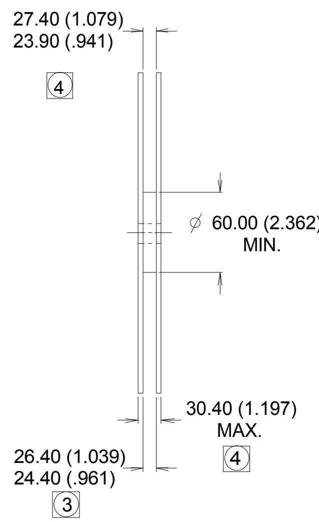


Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

D²Pak (TO-263AB) Tape & Reel Information (Dimensions are shown in millimeters (inches))







NOTES :
1. COMFORMS TO EIA-418.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION MEASURED @ HUB.
4. INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at http://www.irf.com/package/

Qualification Information

Qualification Level		Automotive (per AEC-Q101)	
		Comments: This part number(s) passed Automotive qualification. Infineon's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		D^2-Pak	MSL1
ESD	Machine Model	Class M4 (+/- 800V)† AEC-Q101-002	
	Human Body Model	Class H2 (+/- 4000V)† AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 2000V)† AEC-Q101-005	
RoHS Compliant		Yes	

† Highest passing voltage.

Revision History

Date	Comments
11/13/2015	• Updated datasheet with corporate template • Corrected ordering table on page 1.

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